

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)
-60	55 at V _{GS} = -10 V	- 5	13.5 nC
	70 at V _{GS} = -4.5 V		

FEATURES

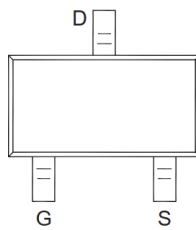
- DT-Trench Power MOSFET
- 175 °C Operating Temperature
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available



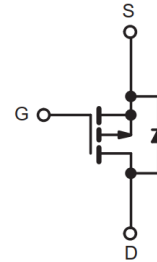
APPLICATIONS

- Notebook PC Core
- VRM/POL

SOT-23-3L Pin Configuration



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C)	I _D	T _C = 25 °C	A
		T _C = 100 °C	
Pulsed Drain Current	I _{DM}	-20	
Avalanche Current Pulse	I _{AS}	-5	
Single Pulse Avalanche Energy	E _{AS}	112	mJ
Continuous Source-Drain Diode Current	I _S	-2.5 ^a	A
Maximum Power Dissipation	P _D	T _A = 25 °C	W
		T _A = 100 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R _{thJA}	40	65	°C/W
Maximum Junction-to-Case	R _{thJC}	4	5.5	

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.

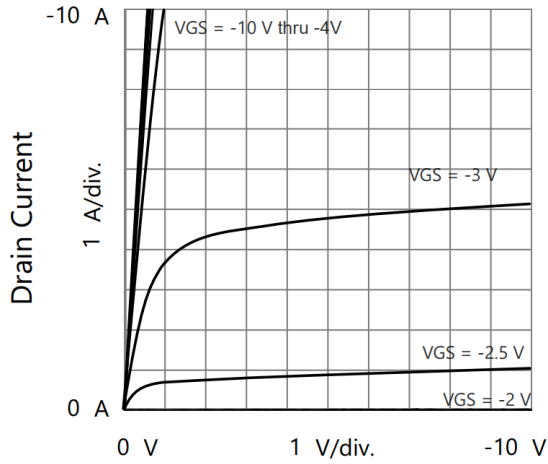
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			-100	μA
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			-500	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -5\text{ V}, V_{GS} = -10\text{ V}$	6			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.2\text{ A}$		55	65	m Ω
		$V_{GS} = -10\text{ V}, I_D = -3.2\text{ A}$		70	85	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -25\text{ V}, I_D = -3.2\text{ A}$		4		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1216		pF
Output Capacitance	C_{oss}			82		
Reverse Transfer Capacitance	C_{rss}			43		
Total Gate Charge	Q_g	$V_{DS} = -48\text{ V}, V_{GS} = -10\text{ V}, I_D = -3.2\text{ A}$		13.5		nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			6.2		
Gate Resistance	R_g	$f = 1\text{ MHz}$		7.5		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 2.5\text{ }\Omega$ $I_D \cong -3.2\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		13		ns
Rise Time	t_r			60		
Turn-Off Delay Time	$t_{d(off)}$			11		
Fall Time	t_f			30		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_A = 25\text{ }^\circ\text{C}$			-5	A
Pulse Diode Forward Current ^a	I_{SM}				-20	
Body Diode Voltage	V_{SD}	$I_S = -1\text{ A}$		-0.6	-1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		80	160	ns
Body Diode Reverse Recovery Charge	Q_{rr}				90	

Notes:

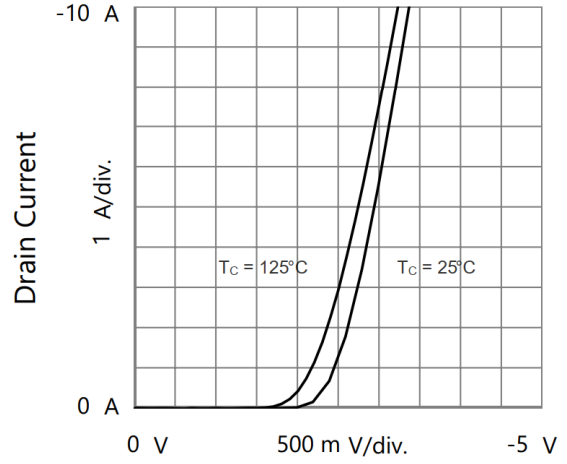
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

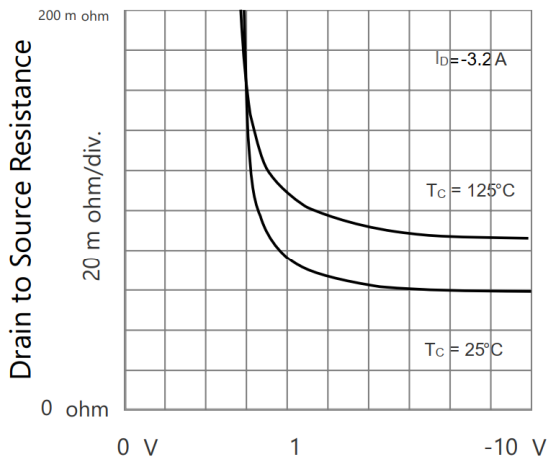
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



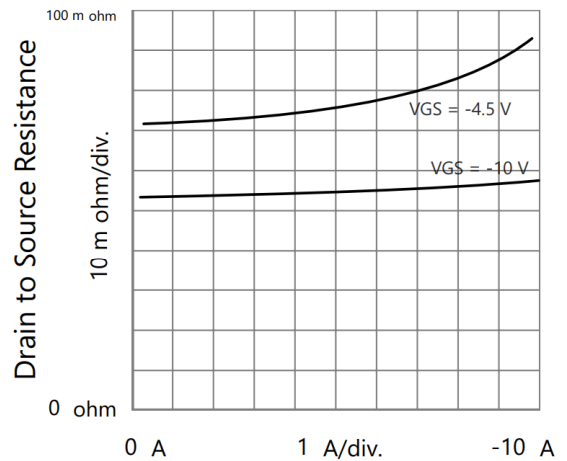
Drain to Source Voltage Output Characteristics



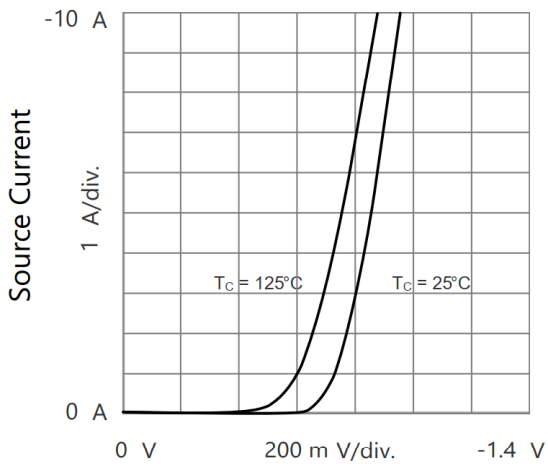
Gate to Source Voltage Transfer Characteristics



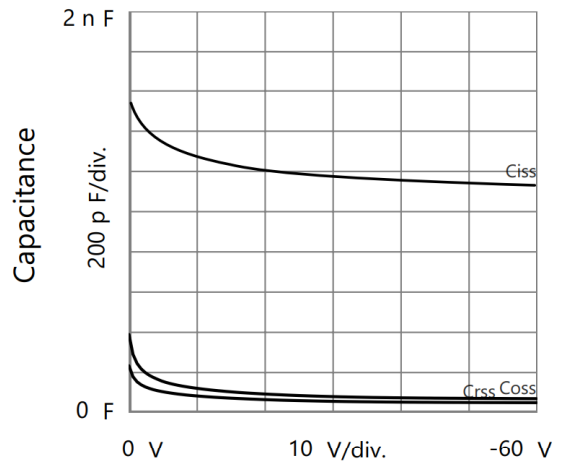
Gate to Source Voltage Drain to Source Resistance vs. Gate to Source Voltage



Drain Current Drain to Source Resistance vs. Drain Current

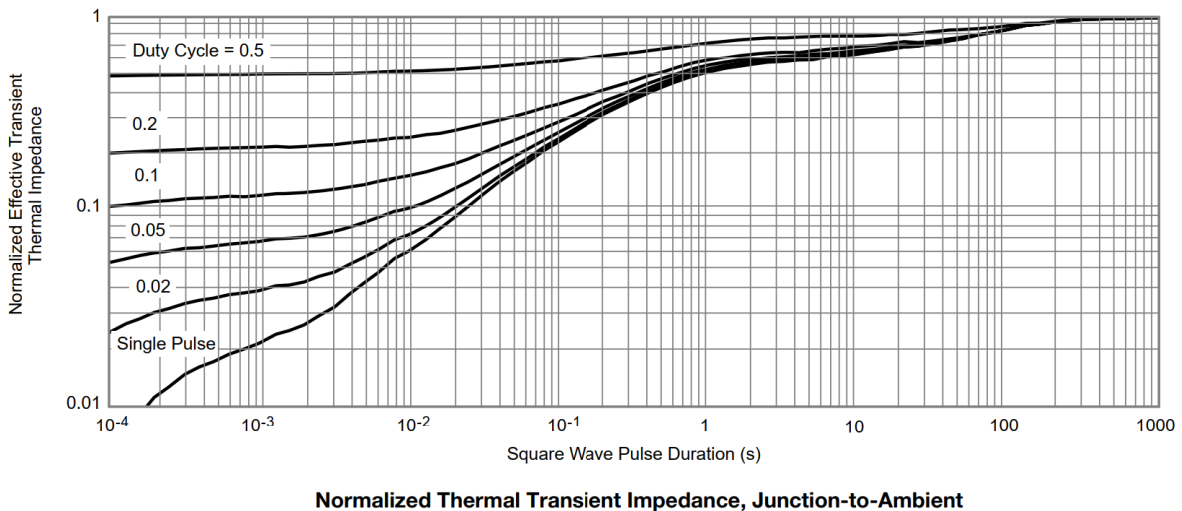
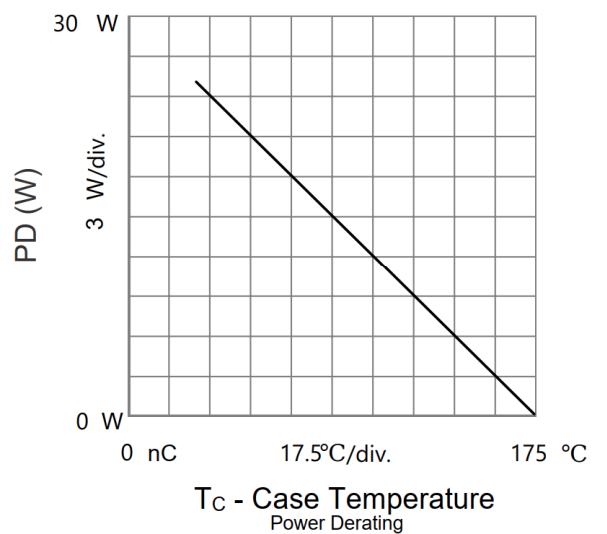
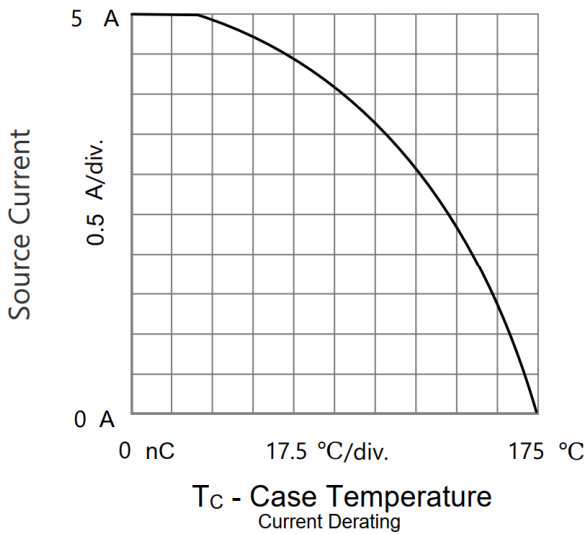
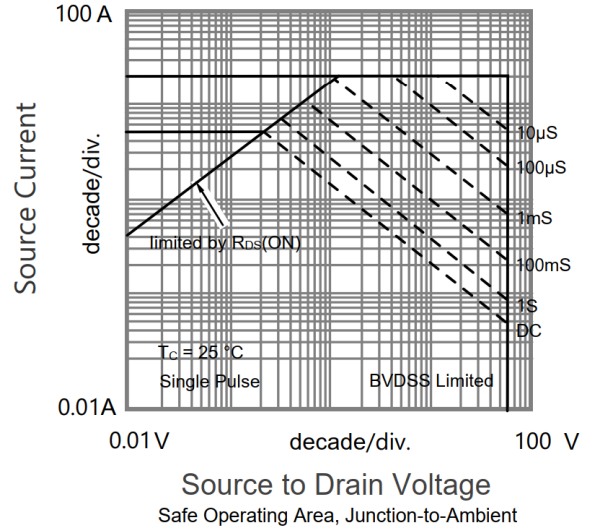
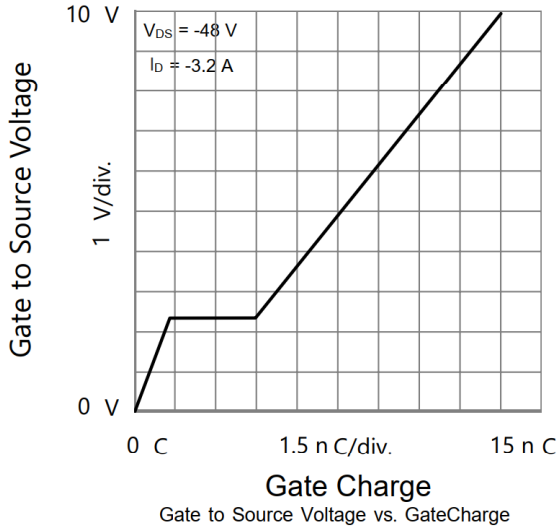


Source to Drain Voltage Body Diode Forward Characteristics

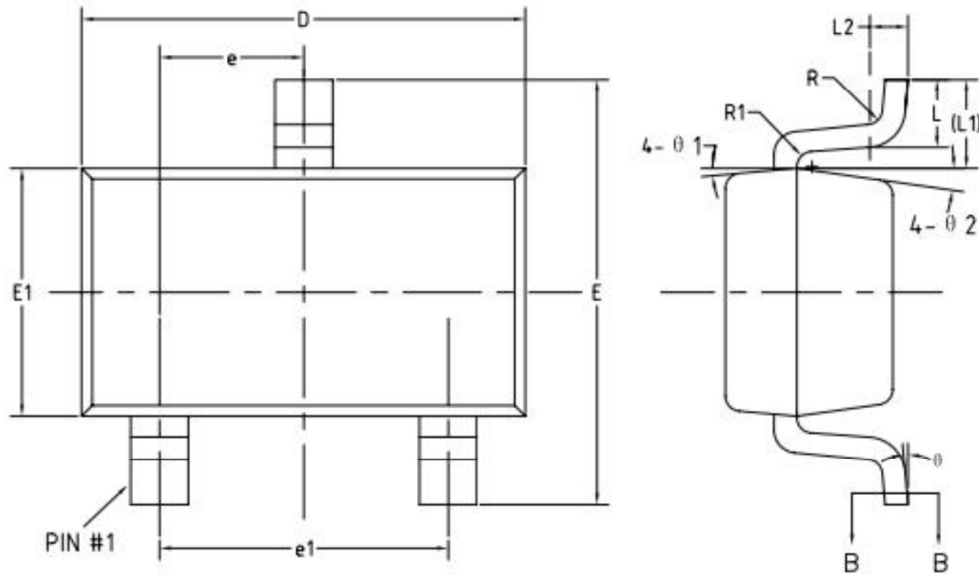


Drain to Source Voltage Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

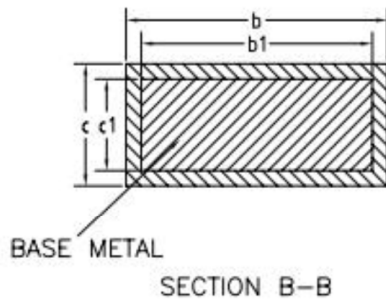


SOT-23-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	-	-	1.50
A1	0.00	-	0.18
A2	0.85	1.10	1.35
A3	0.58	0.65	0.72
b	0.23	-	0.53
b1	0.20	0.40	0.50
c	0.09	-	0.22
c1	0.08	0.13	0.21
D	2.78	2.95	3.10
E	2.58	2.80	3.03
E1	1.55	1.65	1.78
e	0.83	0.95	1.07
e1	1.78	1.90	2.02
L	0.28	0.45	0.62
L1	0.59REF		
L2	0.25BSC		
R	0.04	-	-
R1	0.04	-	0.21
θ	0°	-	8°
θ 1	8°	10°	12°
θ 2	8°	10°	12°



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